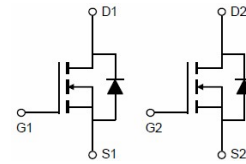


AP6800

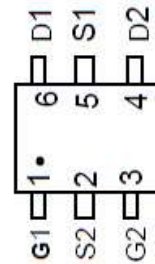
N-Channel Power MOSFET

Description

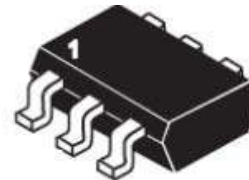
The AP6800 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.



Schematic diagram



Marking and pin Assignment



SOT23-6L top view

General Features

- $V_{DS} = 30V, I_D = 5.8A$
 $R_{DS(ON)} < 32m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 28m\Omega @ V_{GS}=10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Battery protection
- Load switch
- Power management

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP6800	AP6800	SOT23-6			

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	5.8	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	104	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA

AP6800
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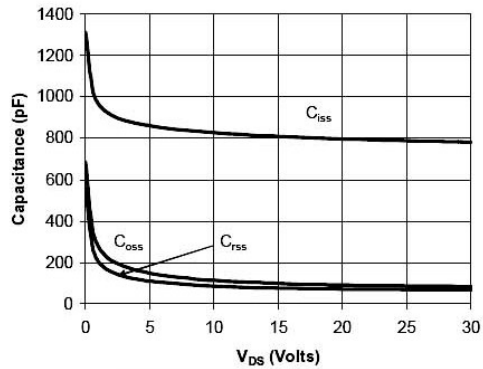
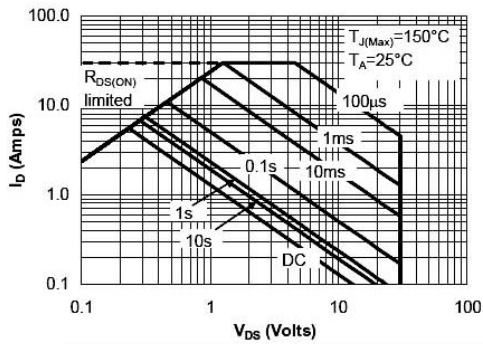
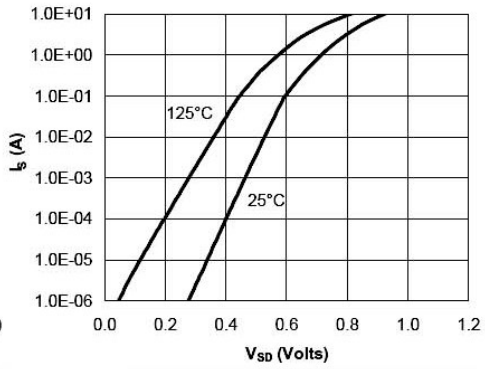
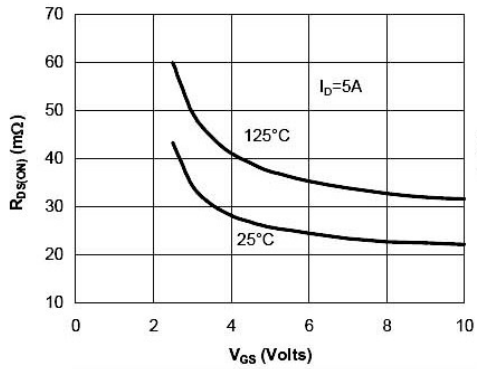
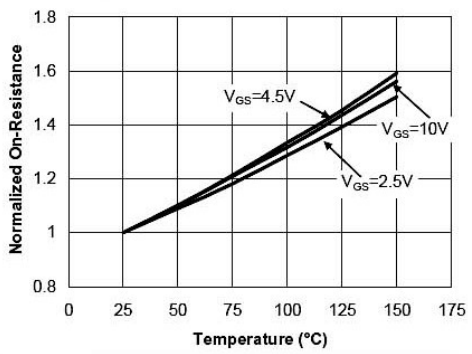
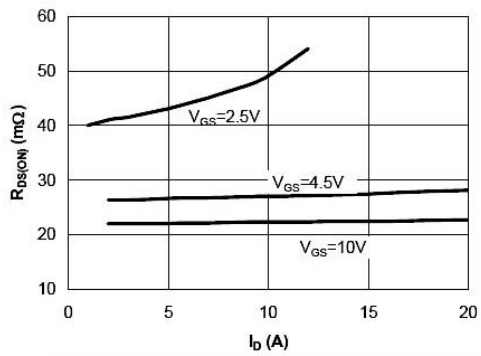
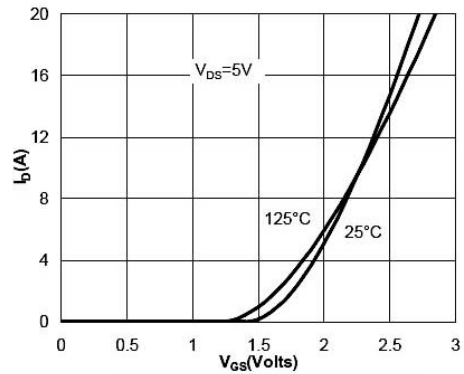
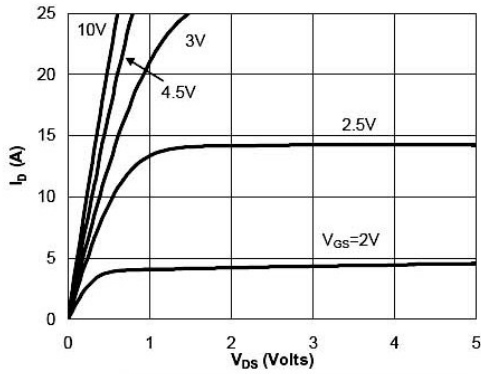
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.7	1.0	1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5.8A$	-	22	28	m Ω
		$V_{GS}=4.5V, I_D=4A$	-	26	70	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=3.5A$	-	10	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	823	-	PF
Output Capacitance	C_{oss}		-	99	-	PF
Reverse Transfer Capacitance	C_{rss}		-	77	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=15V, R_L=4.2\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	3.3	-	nS
Turn-on Rise Time	t_r		-	4.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26.5	-	nS
Turn-Off Fall Time	t_f		-	10.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=3.5A,$ $V_{GS}=10V$	-	4.0	-	nC
Gate-Source Charge	Q_{gs}		-	0.75	-	nC
Gate-Drain Charge	Q_{gd}		-	0.65	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=3.5A$	-	0.8	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	3.5	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

N-Channel Power MOSFET

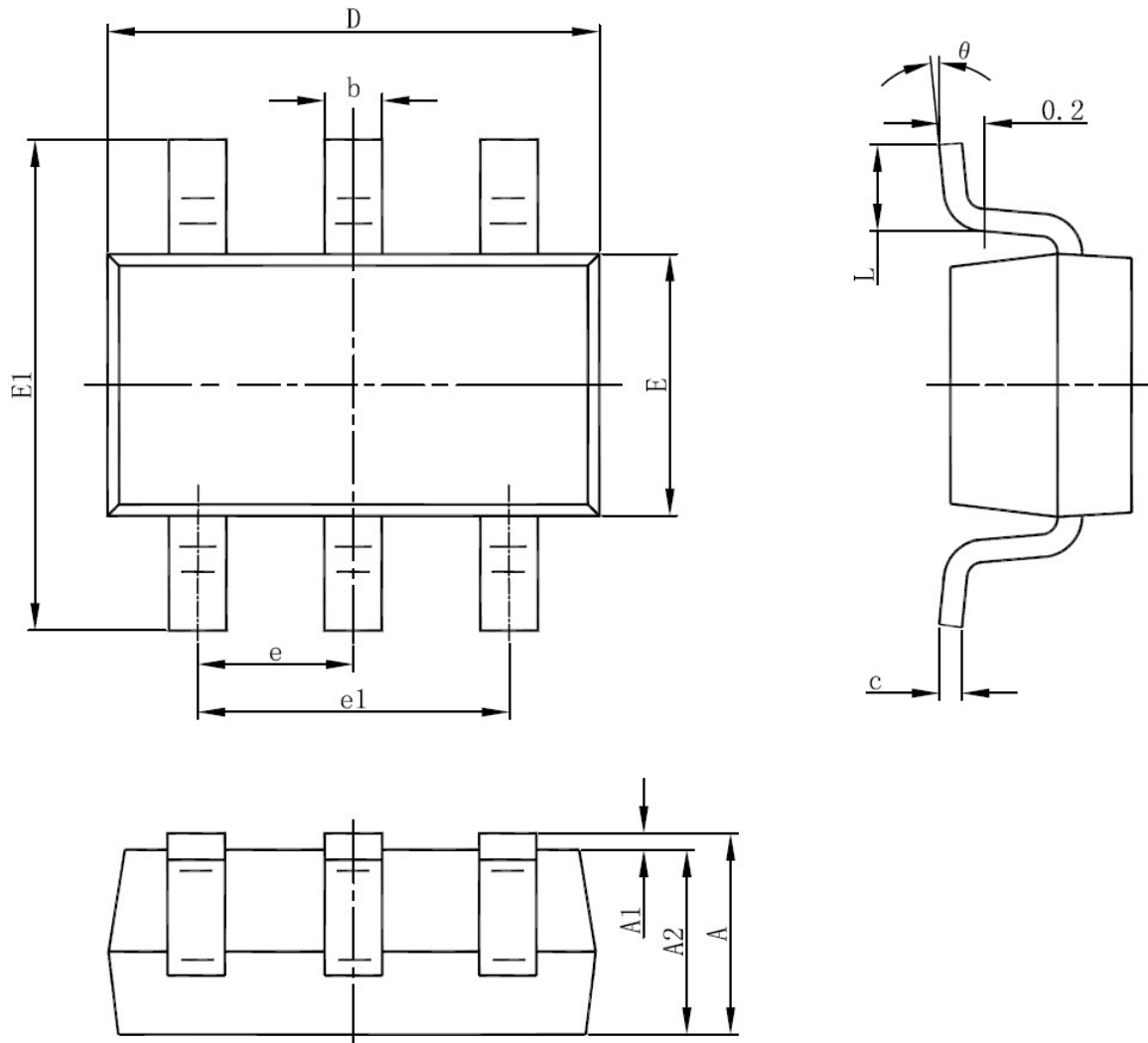
Electrical Characteristic Curve



AP6800

N-Channel Power MOSFET

SOT23-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°